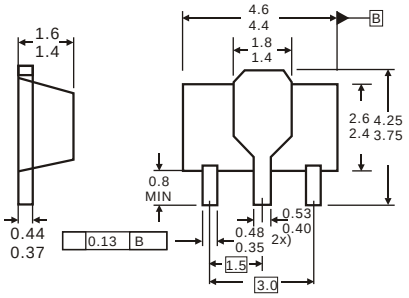
MPSA94

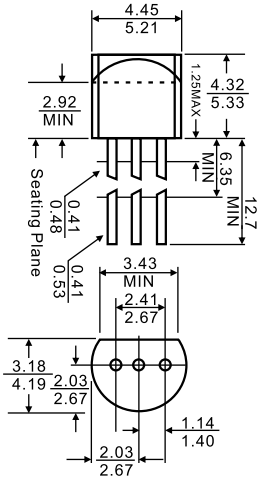
PNP SILICON TRANSISTOR

■ FEATURES

* Collector-Emitter voltage: V_{CEO}=-400V
* Low collector-Emitter saturation voltage



SOT-89



TO-92

Dimensions in inches and (millimeters)

■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
MPSA94L-AB3-R	MPSA94G-AB3-R	SOT-89	B	C	E	Tape Reel
MPSA94L-T92-B	MPSA94G-T92-B	TO-92	E	B	C	Tape Box
MPSA94L-T92-K	MPSA94G-T92-K	TO-92	E	B	C	Bulk

Note: Pin Assignment: B: Base C: Collector E: Emitter

MPSA94G-AB3-R

(1)Packing Type

(2)Package Type

(3)Green Package

(1) R: Tape Reel, B: Tape Box, K: Bulk

(2) AB3: SOT-89, T92: TO-92

(3) G: Halogen Free and Lead Free, L: Lead Free

■ ABSOLUTE MAXIMUM RATING (Operating temperature range applies unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltage		V_{CBO}	-400	V
Collector-Emitter Voltage		V_{CEO}	-400	V
Emitter-Base Voltage		V_{EBO}	-6	V
Collector Power Dissipation (T_A=25°C)	SOT-89	P_D	500	mW
	TO-92		625	mW
Collector Current		I_C	-300	mA
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-40 ~ +150	°C

Note Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

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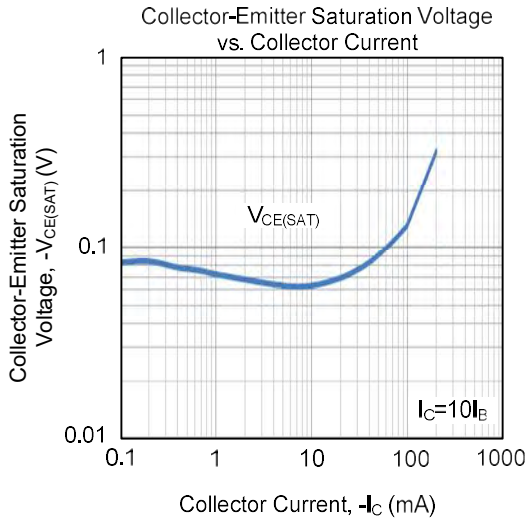
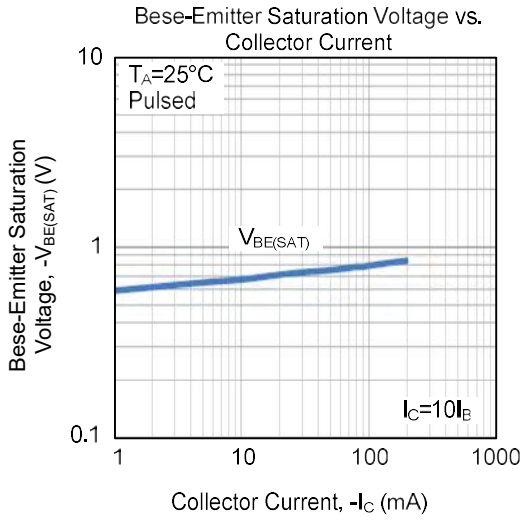
■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV_{CBO}	I_C=-100μA, I_E=0	-400			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C=-1mA, I_B=0	-400			V
Collector-Emitter Breakdown Voltage	BV_{CES}	I_C=-100μA, V_{BE}=0	-400			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I_E=-100μA, I_C=0	-5			V
Collector Cut-off Current	I_{CBO}	V_{CB}=-300V, I_E=0			-100	nA
Collector Cut-off Current	I_{CES}	V_{CE} =-400V, V_{BE}=0			-1	μA
Emitter Cut-off Current	I_{EBO}	V_{EB}=-4V, I_C=0			-100	nA
DC Current Gain(note)	h_{FE}	V_{CE}=-10V, I_C=-1mA V_{CE}=-10V, I_C=-10mA V_{CE}=-10V, I_C=-50mA V_{CE}=-10V, I_C=-100mA	60 70 70 40		300	
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	I_C=-10mA, I_B=-1mA I_C=-50mA, I_B=-5mA			-0.20 -0.5	V
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	I_C=-10mA, I_B=-1mA			-0.75	V
Output Capacitance	C_{ob}	V_{CB}=-20V, I_E=0, f=1MHz			7	pF

Note: Pulse test: Pulse Width<300μs, Duty Cycle<2%.

■ TYPICAL CHARACTERISTICS





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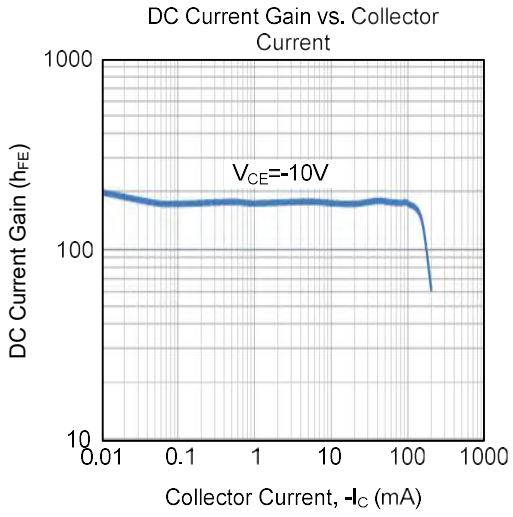
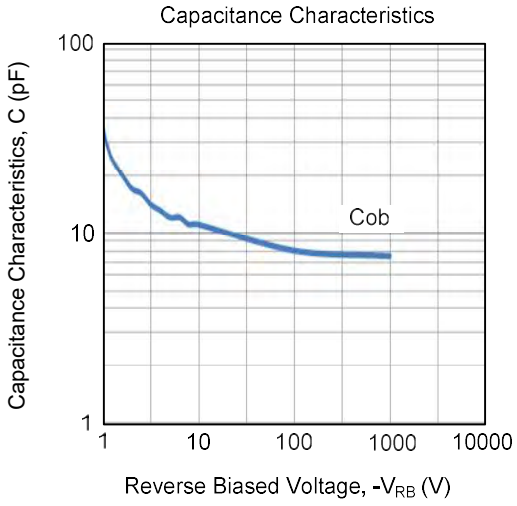
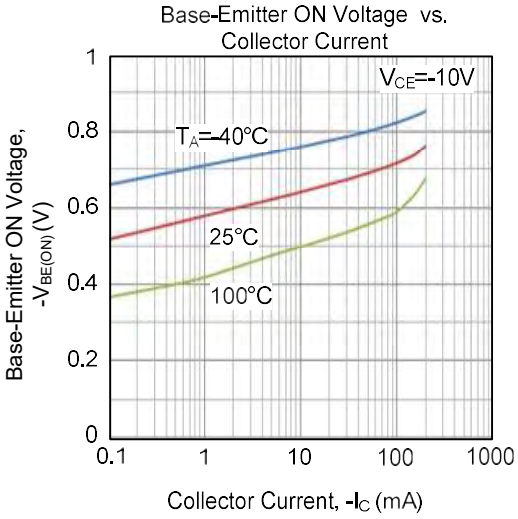
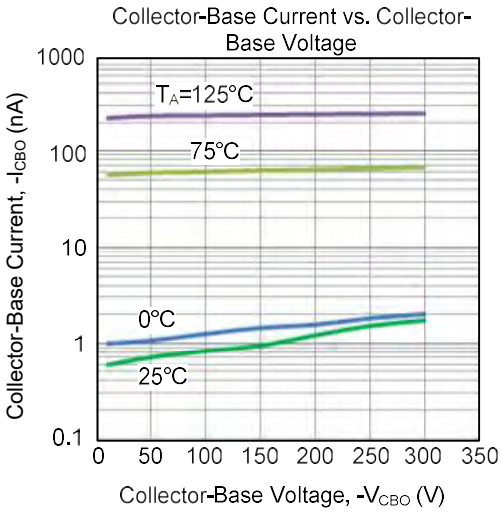
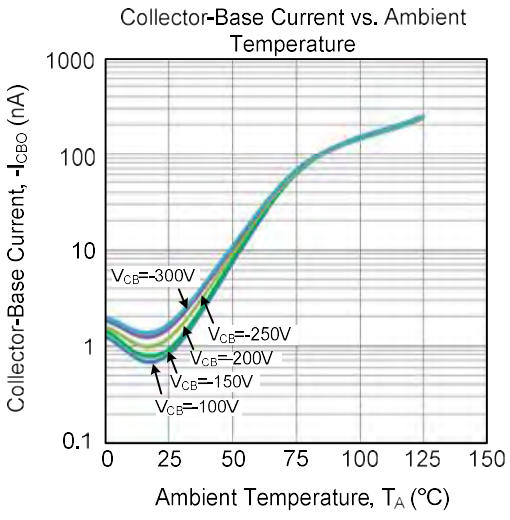
■ TYPICAL CHARACTERISTICS

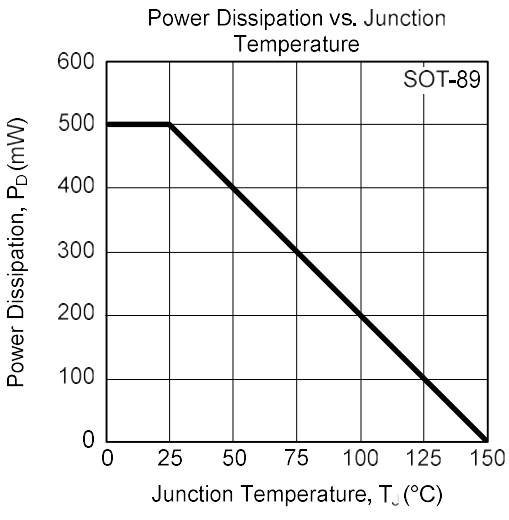












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